41st RD50 Workshop on Radiation Hard Semiconductor Devices for Very High Luminosity Colliders (Sevilla, Spain)

Tuesday, 29 November 2022

Defect and Material Characterization - Salón de Grados, 2nd Floor (09:00 - 10:30)

time	[id] title	presenter
09:00	[58] Welcome	PALOMO PINTO, Francisco Rogelio
09:10	[37] Non-Ionizing Energy Loss in Silicon: Geant4 simulations and defect cluster studies towards more advanced NIEL concept for radiation damage modelling and prediction	SUBERT, Vendula
09:30	[54] Profiling of carrier lifetime and electrical characteristics in PIN and LGAD structures	CEPONIS, Tomas
09:50	[57] Radiation damage investigation of epitaxial p-type Schottky diodes using TCAD simulation	CHEN, Yebo
10:10	[38] Irradiation studies of p-Si using Schottky Diode and PN junction	ZHANG, Dengfeng

Defect and Material Characterization - Salón de Grados, 2nd Floor (11:00 - 13:00)

time	[id] title	presenter
11:00	[34] Multistage impact ionization in Si detectors in situ irradiated at 1.9 K	Mrs SHEPELEV, Artem
11:20	[33] Defect characterization studies and modelling of defect spectra for 60Co gamma-irradiated epitaxial p-type Si diodes	HIMMERLICH, Anja
11:40	[18] Investigation of high resistivity p-type FZ silicon diodes after 60Co - gamma irradiation	LIAO, Chuan
12:00	[1] Effect of Fe-implantation on the electrical characteristics of p-type Si-based diode.	Mr BODUNRIN, Joseph
12:20	[56] Charge carrier mobility evaluation in Silicon Microstrips detectors exploiting megnetoresistivity effect	Dr MEKYS, Algirdas
12:40	[26] Timing resolution and CCE of n-on-n silicon sensors with TCT setup	FERRER NAVAL, Oscar David

Defect and Material Characterization - Salón de Grados, 2nd Floor (14:00 - 15:20)

time	[id] title	presenter
14:00	[16] Understanding the frequency dependence of CV measurements of irradiated silicon detectors	MÄGDEFESSEL, Sven
14:20	[9] Including radiation damage effects in ATLAS MonteCarlo simulations: status and perspectives	BOMBEN, Marco
14:40	[60] Discussion	PINTILIE, Ioana MOLL, Michael